

# High voltage discharge, High speed switching, Low Noise (–60V, –3A)

## 2SA2072

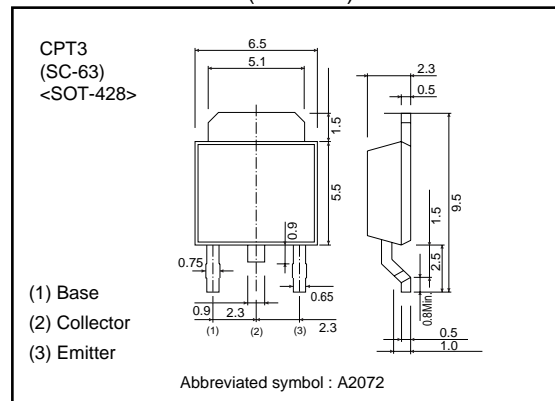
### ●Features

- 1) High speed switching. (Tf : Typ. : 20ns at Ic=–3A)
- 2) Low saturation voltage, typically.  
(Typ. : –200mV at Ic=–2.0A, Ib=–200mA)
- 3) Strong discharge power for inductive load and capacitance load.
- 4) Low Noise.
- 5) Complements the 2SC5825.

### ●Applications

High speed switching, Low noise

### ●External dimensions (Unit : mm)



### ●Structure

PNP silicon epitaxial planar transistor

[www.DataSheet4U.com](http://www.DataSheet4U.com)

### ●Packaging specifications

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	2500
2SA2072		○

### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V <sub>CB0</sub>	–60	V
Collector-emitter voltage	V <sub>CE0</sub>	–60	V
Emitter-base voltage	V <sub>EB0</sub>	–6	V
Collector current	DC	I <sub>c</sub>	–3 A
	Pulsed	I <sub>cP</sub>	–6 A
Power dissipation	P <sub>c</sub>	1.0	W
		10.0	W
Junction temperature	T <sub>j</sub>	150	°C
Range of storage temperature	T <sub>stg</sub>	–55 to 150	°C

\*1 P<sub>w</sub>=100ms

\*2 Ta=25°C

\*3 Tc=25°C

## Transistors

## ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Collector-emitter breakdown voltage	$BV_{CEO}$	-60	-	-	V	$I_C = -1\text{mA}$
Collector-base breakdown voltage	$BV_{CBO}$	-60	-	-	V	$I_C = -100\mu\text{A}$
Emitter-base breakdown voltage	$BV_{EBO}$	-6	-	-	V	$I_E = -100\mu\text{A}$
Collector cut-off current	$I_{CBO}$	-	-	-1.0	$\mu\text{A}$	$V_{CB} = -20\text{V}$
Emitter cut-off current	$I_{EBO}$	-	-	-1.0	$\mu\text{A}$	$V_{EB} = -4\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-200	-500	mV	$I_C = -2\text{A}$ $I_B = -0.2\text{A}$ *1
DC current gain	$h_{FE}$	120	-	270	-	$V_{CE} = -2\text{V}$ $I_C = -100\text{mA}$
Transistor frequency	$f_r$	-	180	-	MHz	$V_{CE} = -10\text{V}$ *1 $I_E = 100\text{mA}$ $f = 10\text{MHz}$
Collector output capacitance	$C_{ob}$	-	50	-	pF	$V_{CB} = -10\text{V}$ $I_E = 0\text{mA}$ $f = 1\text{MHz}$
Turn-on time	$t_{on}$	-	20	-	ns	$I_C = -3\text{A}$ *2 $I_{B1} = -300\text{mA}$ $I_{B2} = 300\text{mA}$ $V_{CC} \approx -25\text{V}$
Storage time	$t_{stg}$	-	150	-	ns	
Fall time	$t_f$	-	20	-	ns	

\*1 Non repetitive pulse

\*2 See switching characteristics measurement circuits

● $h_{FE}$  RANK

Q
120-270

Transistors

●Electrical characteristics curves

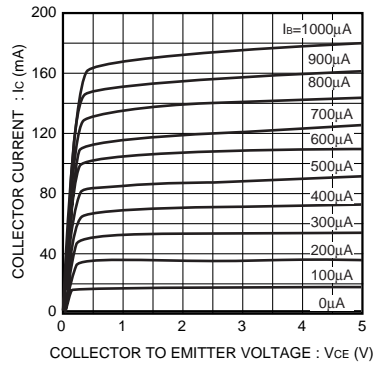


Fig.1 Typical output characteristics

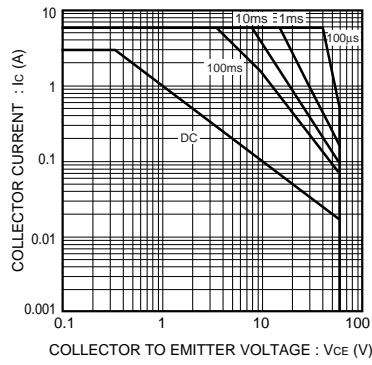


Fig.2 Safe operating area

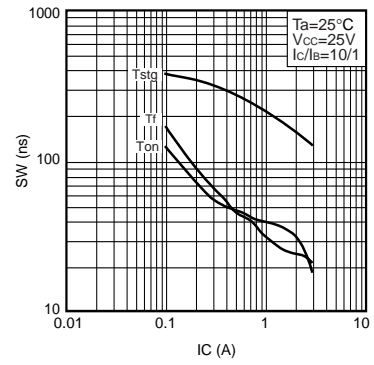


Fig.3 Switching Time

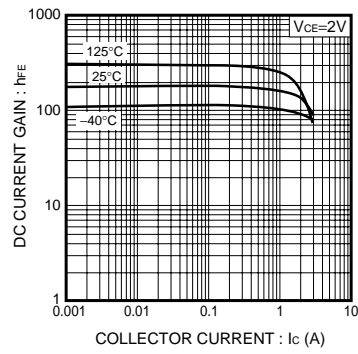


Fig.4 DC current gain vs. collector current ( I )

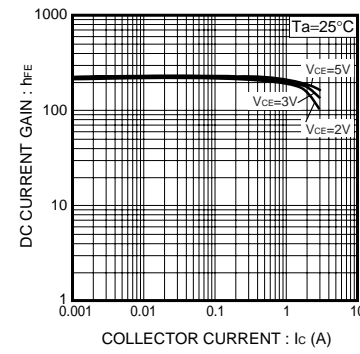


Fig.5 DC current gain vs. collector current ( II )

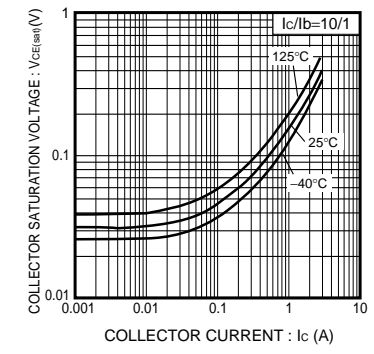


Fig.6 Collector-emitter saturation voltage vs. collector current ( I )

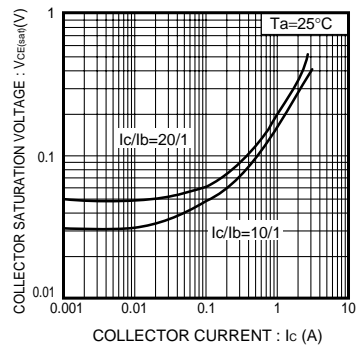


Fig.7 Collector-emitter saturation voltage vs. collector current ( II )

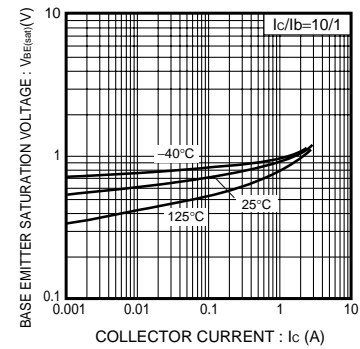


Fig.8 Base-emitter saturation voltage vs. collector current

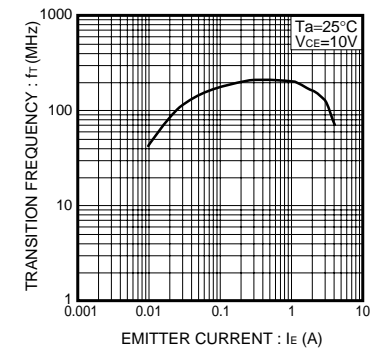


Fig.9 Transition frequency

Transistors

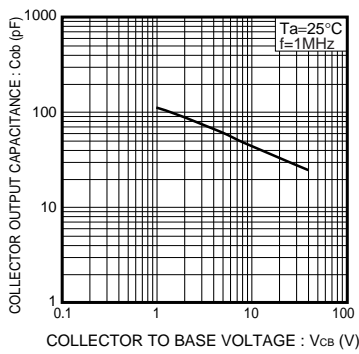


Fig.10 Collector output capacitance

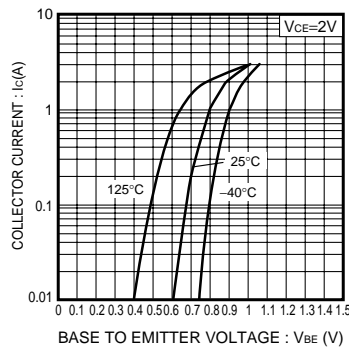
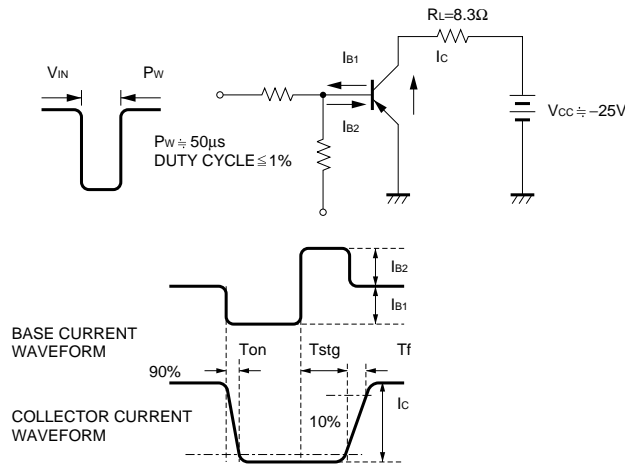


Fig.11 Grounded emitter propagation characteristics

●Switching characteristics measurement circuits



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